

MITSUBISHI IGBT MODULES
CM100DU-24NFH

HIGH POWER SWITCHING USE

CM100DU-24NFH



- IC 100A
- VCES 1200V
- Insulated Type
- 2-elements in a pack

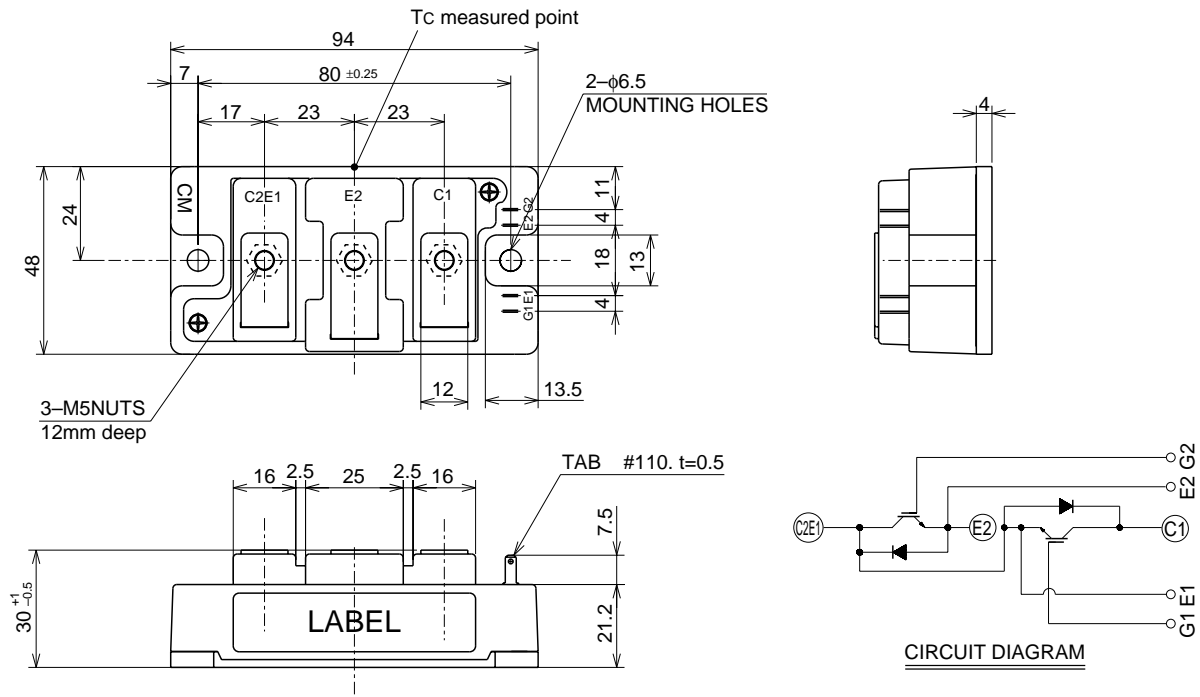
APPLICATION

High frequency switching use (30kHz to 60kHz).
 Gradient amplifier, Induction heating, power supply, etc.

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm

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HIGH POWER SWITCHING USE

MAXIMUM RATINGS (Tj = 25°C)

| Symbol | Parameter | Conditions | Ratings | Unit |
|---------------------------|-------------------------------|--|------------|-------|
| V _{CE} | Collector-emitter voltage | G-E Short | 1200 | V |
| V _{GE} | Gate-emitter voltage | C-E Short | ±20 | V |
| I _C | Collector current | Operation (Note 2) | 100 | A |
| I _{CM} | | Pulse (Note 2) | 200 | A |
| I _E (Note 1) | Emitter current | Operation (Note 2) | 100 | A |
| I _{EM} (Note 1) | | Pulse (Note 2) | 200 | A |
| P _C (Note 3) | Maximum collector dissipation | T _C = 25°C | 560 | W |
| P _C ' (Note 3) | Maximum collector dissipation | T _C ' = 25°C ⁴ | 730 | W |
| T _j | Junction temperature | | -40 ~ +150 | °C |
| T _{stg} | Storage temperature | | -40 ~ +125 | °C |
| V _{iso} | Isolation voltage | Main Terminal to base plate, AC 1 min. | 2500 | V |
| — | Mounting torque | Main Terminal M5 | 2.5 ~ 3.5 | N • m |
| — | | Mounting holes M6 | 3.5 ~ 4.5 | N • m |
| — | Weight | Typical value | 310 | g |

ELECTRICAL CHARACTERISTICS (Tj = 25°C)

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|--------------------------|---|--|--------|------|--------|------|
| | | | Min. | Typ. | Max. | |
| I _{CE} | Collector cutoff current | V _{CE} = V _{CE} , V _{GE} = 0V | — | — | 1 | mA |
| V _{GE(th)} | Gate-emitter threshold voltage | I _C = 10mA, V _{CE} = 10V | 4.5 | 6 | 7.5 | V |
| I _{GE} | Gate leakage current | V _{GE} = V _{GES} , V _{CE} = 0V | — | — | 0.5 | μA |
| V _{CE(sat)} | Collector-emitter saturation voltage (Note 4) | T _j = 25°C, I _C = 100A, V _{GE} = 15V | — | 5.0 | — | V |
| C _{ies} | Input capacitance | T _j = 125°C, I _C = 100A, V _{GE} = 15V | — | 7.0 | — | nF |
| C _{oes} | Output capacitance | V _{CE} = 10V | — | — | 1.6 | nF |
| C _{res} | Reverse transfer capacitance | V _{GE} = 0V | — | — | 0.3 | nF |
| Q _G | Total gate charge | V _{CC} = 600V, I _C = 100A, V _{GE} = 15V | — | 450 | — | nC |
| t _{d(on)} | Turn-on delay time | V _{CC} = 600V, I _C = 100A V _{GE1} = V _{GE2} = 15V R _G = 3.1Ω, Inductive load switching operation I _E = 100A | — | — | 100 | ns |
| t _r | Turn-on rise time | | — | — | 50 | ns |
| t _{d(off)} | Turn-off delay time | | — | — | 250 | ns |
| t _f | Turn-off fall time | | — | — | 150 | ns |
| t _{rr} (Note 1) | Reverse recovery time | I _E = 100A | — | — | 150 | ns |
| Q _{rr} (Note 1) | Reverse recovery charge | | — | 5.0 | — | μC |
| V _{EC} (Note 1) | Emitter-collector voltage | I _E = 100A, V _{GE} = 0V | — | — | 3.5 | V |
| R _{th(j-c)Q} | Thermal resistance*1 | IGBT part (1/2 module) | — | — | 0.22 | °C/W |
| R _{th(j-c)R} | | FWDi part (1/2 module) | — | — | 0.47 | °C/W |
| R _{th(c-f)} | Contact thermal resistance | Case to fin, Thermal compound Applied*2 (1/2 module) | — | 0.07 | — | °C/W |
| R _{th(j-c')Q} | Thermal resistance*4 | IGBT part (1/2 module) | — | — | 0.17*3 | °C/W |
| R _{th(j-c')R} | | FWDi part (1/2 module) | — | — | 0.29*3 | °C/W |
| R _G | External gate resistance | | 3.1 | — | 31 | Ω |

*1 : T_C measured point is shown in page OUTLINE DRAWING.

*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

*3 : If you use this value, R_{th(f-a)} should be measured just under the chips.

*4 : T_C' measured point is just under the chips.

Note 1. I_E, V_{EC}, t_{rr} & Q_{rr} represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).

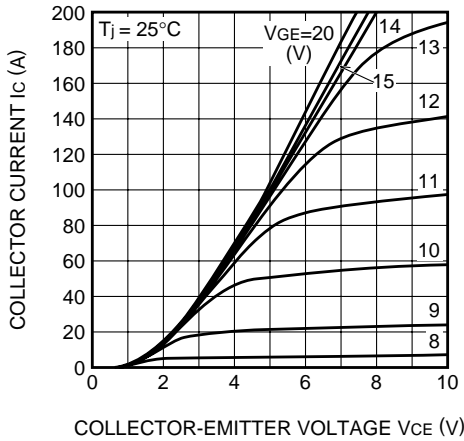
2. Pulse width and repetition rate should be such that the device junction temp. (T_j) does not exceed T_{jmax} rating.

3. Junction temperature (T_j) should not increase beyond 150°C.

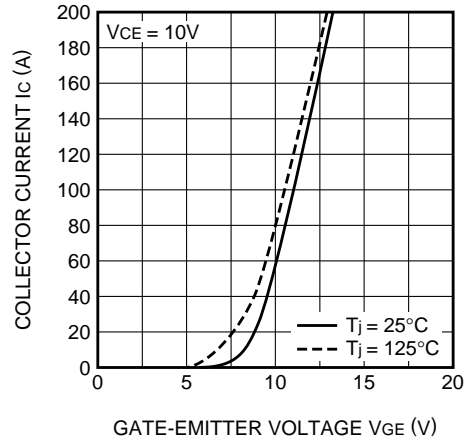
4. No short circuit capability is designed.

PERFORMANCE CURVES

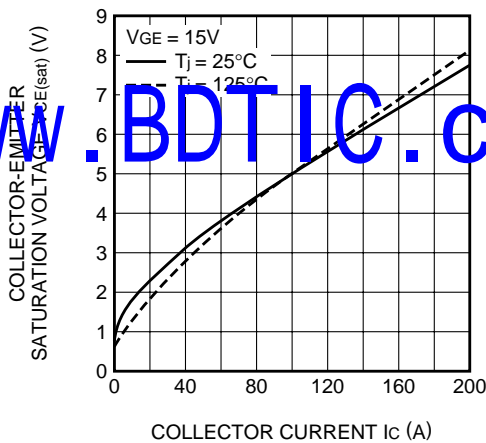
OUTPUT CHARACTERISTICS (TYPICAL)



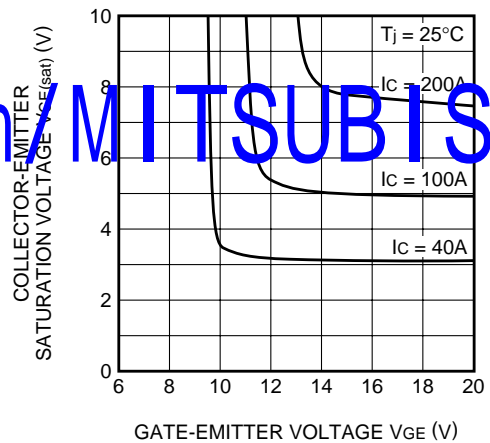
TRANSFER CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

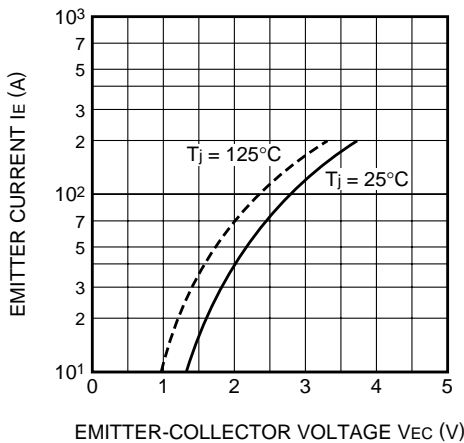


COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

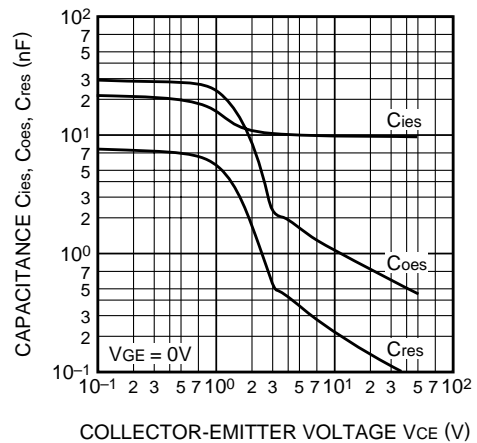


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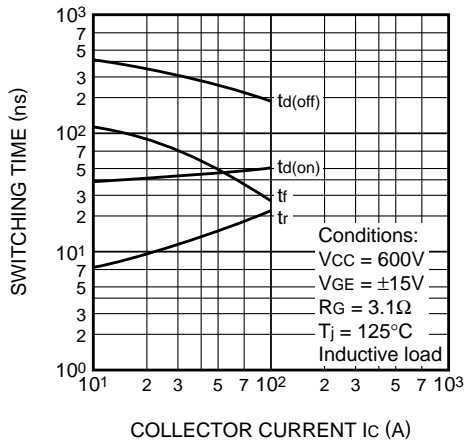
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



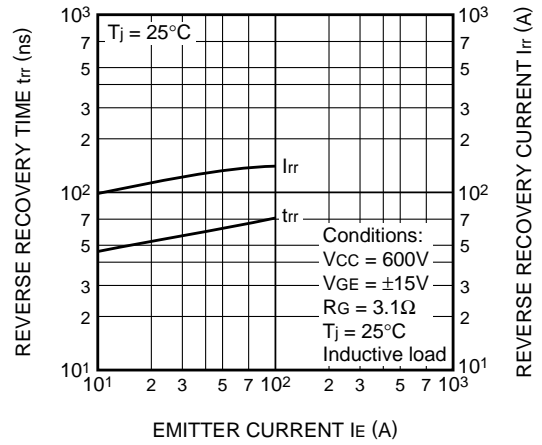
CAPACITANCE CHARACTERISTICS (TYPICAL)



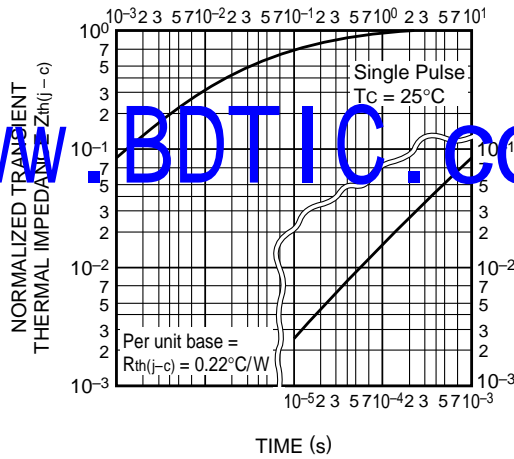
HALF-BRIDGE SWITCHING TIME CHARACTERISTICS (TYPICAL)



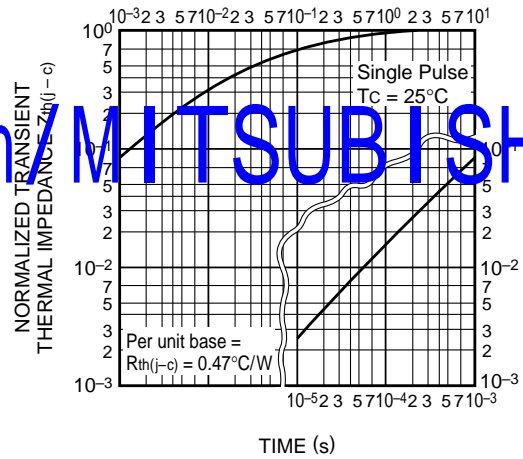
REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL)



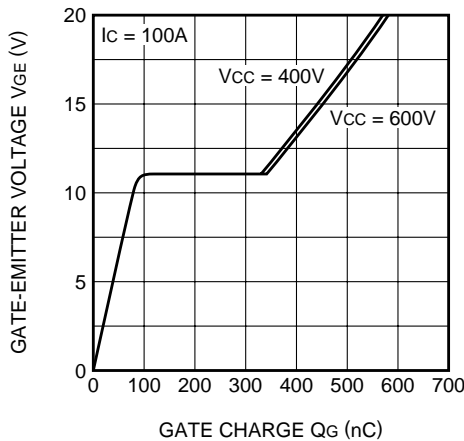
TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (FWDi part)



GATE CHARGE CHARACTERISTICS (TYPICAL)



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